



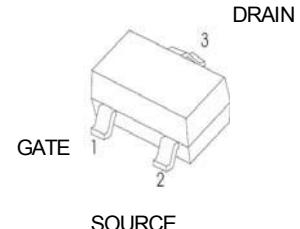
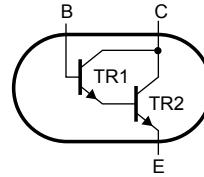
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## BCV27T (KCV27T) Darlington Transistors

### ■ Features

- Medium current (max. 500 mA)
- Low voltage (max. 60 V)
- High DC current gain (min. 20 000).
- Complements to BCV26

Marking FF



SOT-523

### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CBO</sub>	40	V
Collector - Emitter Voltage	V <sub>CEO</sub>	30	
Emitter - Base Voltage	V <sub>EBO</sub>	10	
Collector Current - Continuous	I <sub>C</sub>	500	mA
Collector Current - Pulse	I <sub>CP</sub>	800	
Base Current	I <sub>B</sub>	100	
Collector Power Dissipation	P <sub>C</sub>	150	mW
Thermal Resistance From Junction to Ambient	R <sub>θJA</sub>	500	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to 150	

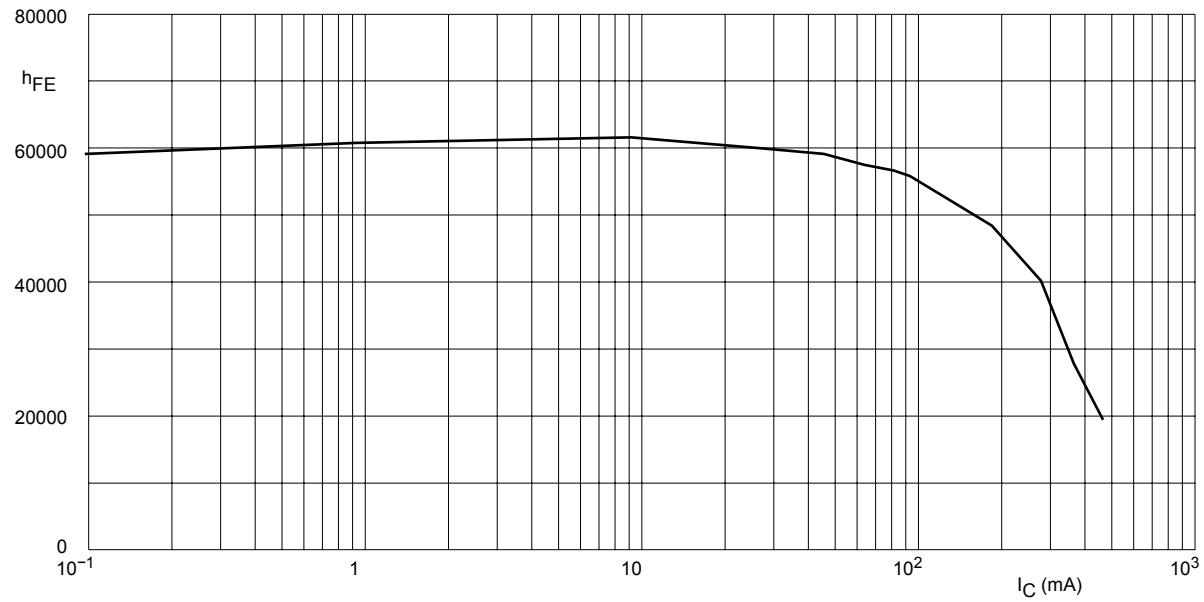
### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = 100 μA, I <sub>E</sub> = 0	40			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0	30			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = 100 μ A, I <sub>C</sub> = 0	10			
Collector-base cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 30 V , I <sub>E</sub> = 0			100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 10V , I <sub>C</sub> =0			100	
Collector-emitter saturation voltage	V <sub>CES(sat)</sub>	I <sub>C</sub> =100 mA, I <sub>B</sub> =0.1mA			1	
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 0.1mA			1.6	V
Base - emitter on-state voltage	V <sub>BE(on)</sub>	V <sub>CES</sub> = 5V, I <sub>C</sub> = 10mA			1.4	
DC current gain	h <sub>FE</sub>	V <sub>CES</sub> = 5V, I <sub>C</sub> = 1mA	4000			
		V <sub>CES</sub> = 5V, I <sub>C</sub> = 10mA	10000			
		V <sub>CES</sub> = 5V, I <sub>C</sub> = 100mA	20000			
Transition frequency	f <sub>T</sub>	V <sub>CES</sub> =5V, I <sub>C</sub> =30mA,f=100MHz		220		MHz



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■ Typical Characteristics



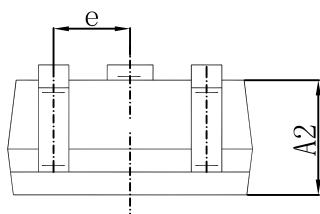
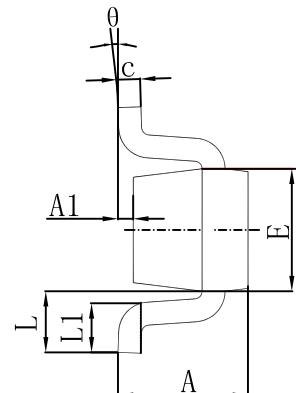
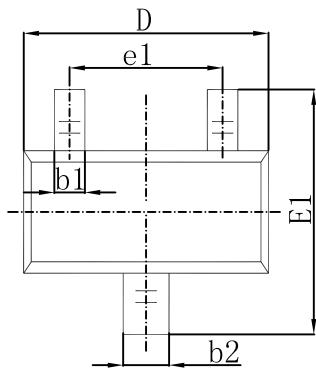
V<sub>CE</sub> = 2 V.

Fig.1 DC current gain; typical values.



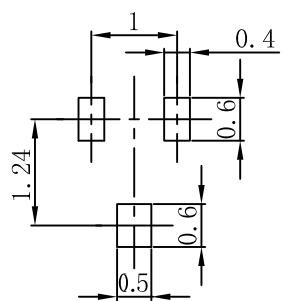
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### SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

### SOT-523 Suggested Pad Layout



#### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.